

ENEE 302 Homework Set 1 Due Th 02/12/04

for all these problems use the mnmosis and mpmosis transistors

#1. 25 points

a) Using Spice plot on the same scale curves of I_D for both NMOS and PMOS transistors. Choose all widths and lengths to be 10μ and bulks tied to sources.

b) Using the P channel width, W_p , as a parameter find by using Spice plots the width which best has the PMOS the complement of the NMOS (that is, such that they both have similar magnitudes of I_D for the same magnitudes of V_{GS} and V_{DS}). Plot on the same graph using $|V_{DS}|$ but actual I_D .

c) Calculate from the plots in a) K_P and V_{TO} and compare with the model parameters.

#2. 25 points

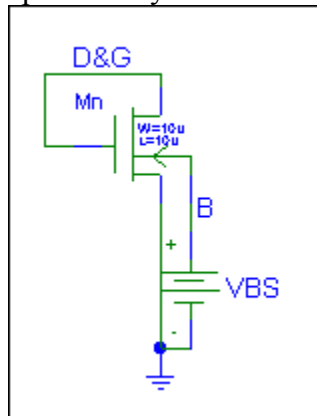
Plot I_C versus V_{CE} with I_B as a parameter for the BN2x4 BJTs.

#3. 25 points

a) For the following NMOS circuit plot the bulk current I_B as a function of the bulk to source voltage for $W=L=10\mu$.

b) Do the same as a parametric run with $10\mu \leq W \leq 50\mu$ in 10μ steps.

b) Repeat for a complementary PMOS circuit.



#4. 25 points

For the following circuit use R_1 as a parameter and in Spice determine its value for $V_{out}=V_{dd}/2$; check analytically.

